TSMC-02-066

February 5, 2004

To: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject: Serial No. 10/600,393 06/20/03

Chi-Chun Chen et al.

METHOD OF FORMING DUAL GATE INSULATOR

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56.

CERTIFICATE OF MAILING

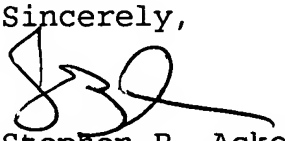
I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on February 9, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date 2/9/04

U.S. Patent 6,294,421 to Gonzalez et al., "Method of Fabricating Dual Gate Dielectric," discloses dual gate dielectric constructions and methods for different regions on an integrated circuit.

Sincerely,



Stephen B. Ackerman,
Reg. No. 37761

Form PTO-1449

INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)	Application Number
TSMC-02-066	10/600,393
Applicant: Chi-Chun Chen et al.	
Filing Date: 06/20/03	Group Art Unit:

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6294421	9/25/01	Gonzalez et al.	438	241	2/18/99

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER	DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.